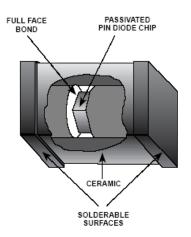
V2

#### **Features**

- Non-Magnetic Package Suitable for MRI Applications
- ♦ Rectangular MELF SMQ Ceramic Package
- ♦ Low R<sub>s</sub> for Low Series Loss
- Longer τ<sub>L</sub> for Low Inter-Modulation Distortion
- High Average Incident Power Handling
- ♦ RoHS Compliant



The MA4P7435NM-1091T is a surface mountable PIN diode in a non-magnetic, Metal Electrode Leadless Faced (MELF) package. The device incorporates M/A-COM Technology's proven HIPAX technology to produce a low inductance ceramic package with no ribbons or whisker wires. The package utilizes M/A-COM Technology's new non-magnetic plating process to provide an extremely low magnetic permeability, hermetically sealed package. Incorporated in the package is a glass passivated PIN chip that is full face bonded on both the cathode and anode to maximize surface area for lower series and thermal resistance. The MA4P7435NM-1091T has been comprehensively characterized both electrically and mechanically to ensure repeatable and predictable performance. The diode is well suited for use in low loss, low distortion, high power switching circuits and is especially designed for use in high magnetic field environments from HF through UHF frequencies. The low thermal resistance of this device also provides excellent performance at high incident RF power levels. This device has been designed to perform well in the most rigorous electrical and mechanical environments.



#### **Designed for Automated Assembly**

These SMQ PIN diodes are designed for high volume tape and reel assembly. The rectangular package design provides for ease of use in most automatic pick and place assembly operations. The parallel flat surfaces are suitable for key jaw or vacuum pickup techniques. All solder able surfaces are tin plated and compatible with reflow and vapor phase soldering methods.

# Absolute Maximum Ratings<sup>1</sup> @ 25°C

Parameter	Absolute Maximum
Operating Temperature	-65°C to +125°C
Storage Temperature	-65°C to +150°C
Diode Junction Temperature	+175°C Continuous
Diode Mounting Temperature	+265°C for 10 seconds
RF C.W. Incident Power	+ 60dBm C.W.
Forward D.C. Current	+500mA
Reverse D.C. Voltage @ -10μA	-1100V

 Exceeding these limits may cause permanent damage.

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

• North America Tel: 800.366.2266 • Europe Tel: +353.21.244.6400

India Tel: +91.80.4155721
 China Tel: +86.21.2407.1588
 Visit www.macomtech.com for additional data sheets and product information.



#### Electrical Specifications @ T<sub>AMB</sub> = +25°C

Test Parameters	Symbol	Units	Conditions	Min.	Тур.	Max.
Total Capacitance	Ст	pF	1MHz / 100V	-	-	3.0 <sup>1</sup>
Series Resistance	$R_s$	Ω	63.6MHz / 100mA	-	-	$0.30^{2,3}$
Series Resistance	Rs	Ω	63.6MHz / 200mA	-	-	0.25 <sup>2,3</sup>
Series Resistance	$R_s$	Ω	63.6MHz / 300mA	-	-	$0.20^{2,3}$
Parallel Resistance	$R_p$	Ω	63.6MHz / 0V	4K	1	-
Forward Voltage	$V_{F}$	V	+100mA		.9	1.0
Reverse Voltage	$V_R$	V	-10µA	1100	-	-
Reverse Current	I <sub>R</sub>	nA	-880V	-	-	100
Carrier Lifetime <sup>4</sup>	T <sub>L</sub>	μS	I <sub>F 10mA</sub> /I <sub>R 6mA</sub>	10	14	-
Thermal Resistance	θ	°C/W	-	-	3	5

- 1. Total capacitance is equivalent to the sum of the chip junction capacitance Cj plus package parasitic capacitance .
- 2. Series resistance R<sub>S</sub> is the sum of the chip to package contact resistance plus junction resistance Rj.
- 3. Rs is measured on an HP4291A.

Commitment to produce in volume is not guaranteed.

4. Measured from 50% of control voltage to 90% of output voltage

#### **Environmental Capability**

MELF devices are applicable for use in commercial and military applications and are designed to meet the environmental requirements of MIL-STD-750, MIL-STD-202 as well as other military standards. The table below lists some of the typical MIL-STD 750 tests the devices are designed to meet.

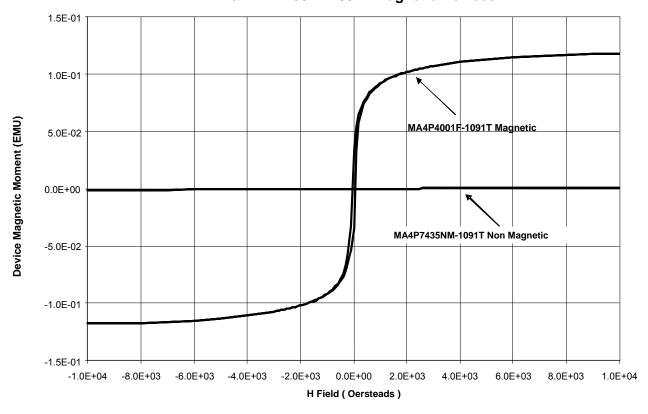
MIL-STD-750			
Test	Method	Description	
High Temperature Storage	1031	+150°C, for 340 Hours	
Temperature Shock	1051	-65°C to +125°C, 20 Cycles	
HTRB	1038	880V, +150°C, for 96 Hours	
Moisture Resistance	1021	No Initial Conditioning, 85% RH, +85°C	
Gross Leak	1071 Cond. E	Dye Penetrant Visual	
Vibration Fatigue	2046	20,000G's, 60 Hz, x, y, z axis	
Solderability	2026	Test Temperature = +245°C	



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#### **Typical Non-Magnetic Performance**

# Comparison of Magnetic Moment for Non Magnetic MA4P7435NM-1091T & MA4P4001F-1091T Magnetic Devices



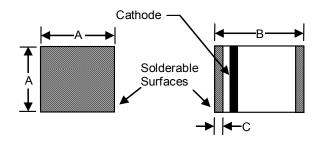
#### <u>Table 1 - Typical Magnetic Properties</u>

# Non-Magnetic MA4P7435NM-1091T vs. Magnetic MA4P4001F-1091T

Magnetic Property	MA4P7435NM-1091T Value	MA4P4001-1091T Value
Saturation Moment (EMU)  @ H = H <sub>MAX</sub> Oersteads	1.0 x E-3	1.2 x E-1
Remanance Moment (EMU)  @ H = 0 Oersteads	1.5 x E-6	3.4 x E-2
Coercivity (Oersteads) @ EMU = 0 Moment	3.0	51.3

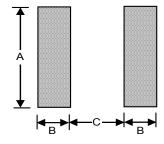


#### **Mechanical Outline**



Case Style 1091 Dimensions in Inches (mm)			
A Square	В	С	
Min. / Max.	Min. / Max.	Min. / Max.	
0.138 / 0.155 (3.50/ 3.94)	0.180 / 0.200 (4.57/ 5.08)	0.008 / 0.030 (.203 / .762)	

#### **Circuit Pad Layout**



Dimension	Package Style 1091	
	inches	mm
Α	0.150	3.81
В	0.050	1.27
С	0.100	2.54

#### **Ordering Information**

Part Number	Package
MA4P7435NM-1091T	Tape and Reel (500pcs/reel)

Commitment to produce in volume is not guaranteed.

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